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Correction: Effects of Ga–Te interface layer on the potential barrier height of CdTe/GaAs heterointerface

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Correction for 'Effects of Ga–Te interface layer on the potential barrier height of CdTe/GaAs heterointerface' by Shouzhi Xi *et al.*, *Phys. Chem. Chem. Phys.*, 2016, **18**, 2639–2645.

Due to a calculation error, the authors would like to replace Fig. 5 in the original article with the revised version shown below:

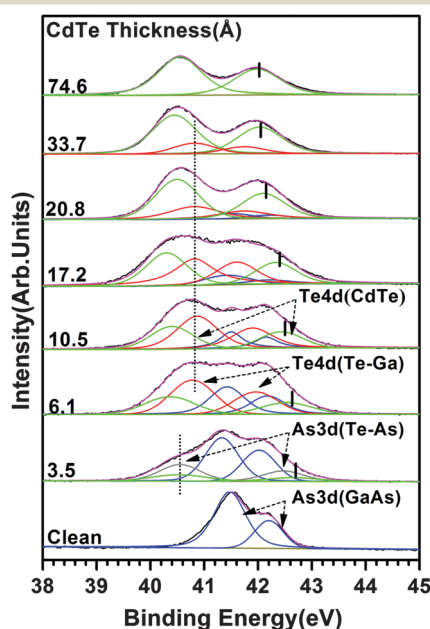


Fig. 5 Evolution of Te 4d and As 3d core levels from GaAs, CdTe, As–Te, and Ga–Te reactions at CdTe/GaAs heterointerface for various CdTe thicknesses measured by SRPES, obtained at normal emission with a photon energy of 90 eV. Black line: experiment results. Purple line: results of the best fit. Fitted with As 3d from GaAs (blue line), As 3d from Te–As reaction (gray line), Te 4d from CdTe (green line), and Te 4d from Ga–Te reaction (red line) components.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

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